

Title (en)
VERTICAL POWER MOSFET

Title (de)
VERTIKALER LEISTUNGS-MOSFET

Title (fr)
TRANSISTOR A EFFET DE CHAMP MOS VERTICAL DE PUISSANCE

Publication
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Application
EP 98947303 A 19980717

Priority
• DE 9802020 W 19980717
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Abstract (en)
[origin: DE19730759C1] The invention relates to a vertical power MOSFET, comprising additional zones (11, 12) arranged in an inner zone (1), said zones having the same and inverse type of conductivity as the inner zone (1). The charge carrier service life is reduced in the additional zones (12) having the same conductivity as the inner zone (1). The additional zones (11, 12) are dimensioned in such a way that the space charge zone practically does not exceed the edge opposite to the upper surface of the MOSFET in the additional zone (12) having the same conductivity as the inner zone (1).

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IPC 8 full level
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CPC (source: EP US)
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